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Programming EEPROM on the MC68HC811E2 during Program Execution

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Introduction

The MC68HC811E2 microcontroller (MCU) has the largest EEPROM array in the MC68HC11 Family of microcontrollers. This 2-K array of EEPROM can be used for both program code and data values. In addition to the 2-K array of EEPROM, the device has 256 bytes of RAM. While some users may choose to use RAM for program variables during execution, others may want to store data and variables in the non-volatile EEPROM, so that data will still be valid after a power-off and power-on sequence.

The Problem

For expanded mode applications of this part, Motorola publishes programming and erasing algorithms in the technical data book for the MC68HC811E2, Motorola document order number MC68HC811E2/D. However, in single-chip mode applications, the only memory resources available for program code are the internal RAM and EEPROM. Code which programs or erases internal EEPROM cannot reside in internal EEPROM. The only other memory resource is RAM, which cannot





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contain program code immediately after power-up because of its volatile nature. Therefore, code in EEPROM must copy the programming algorithm into RAM, load parameters into the registers or in global RAM variables, and then jump (JSR) to the programming algorithm copy in RAM.

At the end of the subroutine, execution resumes in EEPROM, and the data is stored until it is erased using the same procedure.

Users often wonder why code executing out of internal EEPROM cannot write to or erase EEPROM, especially users of the MC68HC811E2, where the only other memory resource in single-chip applications is the internal RAM.

Programming and erasing of EEPROM requires applying a high voltage to the EEPROM array. In MC68HC11 devices, this programming voltage is developed with an on-chip charge pump.

High voltage is applied to the EEPROM array only when the EEPGM bit in the PPROG register is set to logic 1. While high voltage is applied to the EEPROM array, the read circuitry in the EEPROM array is disabled. This is why programs that try to use the programming algorithm while executing code from EEPROM "hang" or "get lost." After turning on the high voltage, the processor executes a read cycle to fetch the opcode for the next instruction. Because the internal EEPROM read circuitry is disabled, the processor can no longer fetch opcodes.



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The Solution

The Solution

The code listing provided here shows how to overcome the problem of programming EEPROM in single-chip applications. The code will work in expanded mode applications as well; however, expanded mode applications simply need to put programming and erase algorithms in an external memory resource to overcome this problem.

The code segment has three major portions:

- The main routine, which initializes the stack pointer, clears the EEPROM block protection register (BPROT), and calls the other routines
- The cpy2ram routine, which copies the algorithms from EEPROM to RAM
- The program, erase, and delay algorithms for EEPROM

The code in the main routine illustrates four important points:

- First, every program must initialize the stack pointer. This must happen before any subroutine calls, interrupts, or pushes and pulls from the stack occur.
- Next, the BPROT register (or single bits in the BPROT register)
 must be cleared within the first 64 clock cycles after reset, so that
 the EEPROM array is not protected from programming and
 erasure.
- If an application separates data and program space, then only the bits which protect data space should be cleared. The main routine calls cpy2ram to ensure that the algorithms are in place every time out of reset.
- Finally, the main routine shows how to set up the parameters and call the program and erase routines. Parameter passing schemes may use registers, specified RAM locations, or the stack.

This code segment only programs one byte of data to the EEPROM. Additional instructions could be substituted for lines 19 through 23, for instance, to fetch data from the serial communications interface (SCI). Each individual byte could then be programmed into EEPROM by calling the bytprgram routine.

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Sample Code

sample Code	•				
EE811.ASM A	ssembled	with I	ASM	02/15/1993	16:05
0000	1	ramhi	equ	\$00ff	;last address of internal RAM
0000	2	regbas	_		;register base address
000	3	bprot	equ		offset from base for BPROT
0000	4	pprog	-		offset from base for PROG
0000	5	eestrt	_		;first address EEPROM on
			_	·	;811E2
	6				
0000	7	rsetve	ec equ	•	;address of reset vector
0000	8	ersrar	n equ	\$0000	;the address in RAM that
	9				routines will be copied to
	10				
FFFE	11	org		rsetvec	reset points to main
FFFEF800	12	fdb			main
-000	13				
F800	14	org		eestrt	<pre>;main begins at start of ;eeprom</pre>
F800 8E00FF	15	main	lds	#ramhi	;set the stack pointer
F803 CE1000	16		ldx	#regbas	;used for index X access
F806 6F35	17		clr	bprot,x	<pre>;clear reg for eeprom prog ;and erase</pre>
F808 BDF81C	18		jsr	cpy2ram	copy routines to ram on the
F80B 18CEF800	19		ldy	#eestrt	;load address parameter into ;index Y
F80F 9D00	20		jsr	ersram	;for sample byte erase
F811 18CEF800			ldy	#eestrt	then program it to \$00
F815 8600	22		ldaa	#\$00	;get data parameter into Acc A
F817 BD0020	23		jsr	bytprg	;REMEMBER: you must jump to
	24		,	1 1 3	;in RAM not those in EEPROM
F81A 20FE	25	bra *			;infinite self-loop to ends
	26				;example
	26 27				;this subroutine will copy the
	27				;program, byte erase
	28				; and delay 10 ms routines into ; RAM at address \$0100
	29				this will let the user
	2,7				; jumpsubroutine to these
					routines
	30				;which will allow proper
					;programming of the EEPROM
	31				;on the 811E2
=01 0 0 =	32	_	,		
F81C 3C	33	cpy2ra			
F81D 183C	34		pshy		
F81F CEF837 F822 18CE0000	35 36		ldx ldy	_	
LOZZ TOCEOOO	30		тау	#ersram	



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F826 E600	37	cpyloop ldab 0,x	
F828 18E7	00 38	stab 0,y	
F82B 08	39	inx	
F82C 1808	40	iny	
F82E 8CF8	6E 41	cpx #endprg	
F831 26F3	42	bne cpyloop	
F833 1838	43	puly	
F835 38	44	pulx	
F836 39	45	rts	
	46		
	47		this subroutine expects the
			;address of the byte to be
	48		erased to be passed in the y
			;register, and pprog is
	49		declared in an equate file
F837 3C	50	byteras pshx	;make reentrant and
F838 37	51	pshb	;save registers
F839 CE10	00 52	ldx #regbas	;used indexed x access
F83C C616		ldab #\$16	;eelat=1, byte erase
F83E E73B	54	stab pprog,x	· •
F840 18E7	00 55	stab 0,y	access byte pointed to by Y
F843 C617		ldab #\$17	turn on eepgm
F845 E73B		stab pprog,x	15
F847 8D05		bsr delay10	relative addressing is
	59	•	;location independent!
F849 6F3B		clr pprog,x	turn off eepgm and eelat
F84B 33	61	pulb	13
F84C 38	62	pulx	restore registers
F84D 39	63	rts	5
F84E	64	enderas equ *	
	65	-	
	66		; this subroutine delays the mcu
			for 10 milliseconds
F84E 3C	67	delay10 pshx	;make reentrant and
	68		;save registers
F84F CE0D	05 69	ldx #\$0d05	constant for 10mS at 2MHz
			;E-clock
F852 09	70	loop10 dex	
F853 26FD	71	bne loop10	relative addressing is
	72		;position independent
F855 38	73	pulx	restore registers;
F856 39	74	rts	
F857	75	enddly equ *	
	76		
	77		;this subroutine programs the
			;byte whose address is in
	78		register y with the value
			;passed in register a
F857 3C	79	bytprg pshx	;make reentrant and
F858 37	80	pshb	;save registers
F859 CE10	00 81	ldx #regbas	for indexed x access
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F85C C602	82	ldab	#\$02	;eelat=1, eepgm=0
F85E E73B	83	stab	pprog,x	
F860 18A700	84	staa	0,y	<pre>;write data to address</pre>
	85			;pointed to by Y
F863 C603	86	ldab	#\$03	;eepgm=1
F865 E73B	87	stab	pprog,x	1 5
F867 8DE5	88	bsr	delay10	relative addressing is
100. 0220	89	222	a3_a7_5	position independent
F869 6F3B	90	clr	pprog,x	;eelat=eepgm=0
F86B 33	91	pulb	PP109/11	, cerae ceps o
F86C 38	92	pulx		restore registers
F86D 39	93	rts		, restore registers
1002 37	95	105		
F86E		zram egud	elav10-byt	teras ;compute
1001	J	ram equa	crayro by	addresses for the routines
	97			that will be in RAM
F86E		prq equ	bytprg-by	
1001	99	prg cqu	Dychia Di	ccias
	100			
	100			
Symbol Table				
27201 10.210				
BPROT		0035		
BYTERAS		F837		
BYTERSRAM		0000		
BYTPRG		F857		
BYTPRGRAM		0020		
CPY2RAM		F81C		
CPYLOOP		F826		
DELAY10		F84E		
DLYRAM		0017		
EESTRT		F800		
ENDDLY		F857		
ENDERAS		F84E		
ENDPRG		F86E		
LOOP10		F852		
MAIN		F800		
PPROG		003B		
RAMHI		00FF		
REGBAS		1000		

FFFE

This code was assembled using IASM11 from P&E Microsystems on an IBM-compatible PC.

RESETVECTOR





Engineering Bulletin Conclusion

Conclusion

The MC68HC811E2 is a unique member of the MC68HC11 Family because of its large EEPROM array. This memory resource is available to users for program space, as well as for data and variables. Single-chip application designers can run into trouble trying to use the EEPROM for variables if they do not realize that internal EEPROM programming or erase algorithms cannot be executed from internal EEPROM.

Once the solution discussed in this engineering bulletin is implemented, users will be able to successfully use the MC68HC811E2 to its full potential in control applications.



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